

# isc N-Channel Mosfet Transistor

# STD13NM60ND

### • FEATURES

- Drain Current ID= 11A@ TC=25  $^{\circ}\mathrm{C}$
- · Drain Source Voltage-
  - : V<sub>DSS</sub>=600V(Min)
- · Fast Switching Speed
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • APPLICATIONS

Switching applications

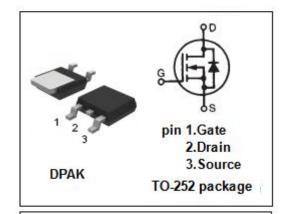


## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	600	V
V <sub>GS</sub>	Gate-Source Voltage	±25	V
I <sub>D</sub>	Drain Current-continuous@ T <sub>C</sub> =25℃	11	А
I <sub>DM</sub>	Pulse Drain Current	44	А
P <sub>tot</sub>	Total Dissipation@T <sub>C</sub> =25℃	110	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.14	°C/W



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	DIM	MIN	MAX	
	Α	6.40	6. 60	15
	В	5. 20	5.40	
	D	1. 15 5. 70	1.35 6.10	
	F		6. 10	
	G	0. 65 0. 75		
	Н	2. 10	2. 50	
	J	2.10	2.40	
				1
	K	0.40	0.60	
		0. 40 0. 90 9. 90	0. 60 1. 10 10. 1	

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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =250μA	3		5	V
V <sub>SD</sub>	Diode Forward On-Voltage	I <sub>S</sub> =11A;V <sub>GS</sub> = 0			1.6	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =5.5A			380	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0			1	- μΑ
		V <sub>DS</sub> = 600V; T <sub>C</sub> =125℃			100	

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